	BAV	70 / 74		
		3 4 <i>I</i> <i>MARKING</i> <i>I</i> <i>BAV74</i> JA	Connection I	Diagram
_	nal Diode			
bsolute	Maximum Ratings * T _A = 25°C un	less otherwise noted	Value	Units
bsolute Symbol		less otherwise noted BAV70 BAV74	Value 70 50	Units V V
Symbol	Maximum Ratings * T _A = 25°C un Parameter	BAV70	70	V
Symbol V _{RRM}	Maximum Ratings * TA = 25°C un Parameter Maximum Repetitive Reverse Voltage Average Rectified Forward Current Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second	BAV70 BAV74	70 50 200 1.0	V V mA
Absolute Symbol V _{RRM} IF(AV)	Maximum Ratings * T _A = 25°C un Parameter Maximum Repetitive Reverse Voltage Average Rectified Forward Current Non-repetitive Peak Forward Surge Current	BAV70 BAV74	70 50 200	V V mA
Absolute Symbol V _{RRM} I _{F(AV)} I _{FSM} T _{STG} T _J	Maximum Ratings * TA = 25°C un Parameter Maximum Repetitive Reverse Voltage Average Rectified Forward Current Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond Storage Temperature Range Operating Junction Temperature	BAV70 BAV74	70 50 200 1.0 2.0	V V mA A A
Absolute Symbol VRRM IFSM TSTG TJ These ratings are OTES: These ratings are These ratings are These ratings are These ratings are These ratings are These ratings are These ratings are	Maximum Ratings * TA = 25°C un Parameter Maximum Repetitive Reverse Voltage Average Rectified Forward Current Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond Storage Temperature Range Operating Junction Temperature Imiting values above which the serviceability of the diode replaced on a maximum junction temperature of 150 degree by limits. The factory should be consulted on applications in Characteristics	BAV70 BAV74 may be impaired.	70 50 200 1.0 2.0 -555 to +150 -555 to +150 150	V V mA A A °C °C
Symbol Symbol ARRM F(AV) FSM STG STG J hese ratings are DTES: These ratings are These ratings are	Maximum Ratings * T _A = 25°C un Parameter Maximum Repetitive Reverse Voltage Average Rectified Forward Current Non-repetitive Peak Forward Surge Current Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond Storage Temperature Range Operating Junction Temperature Ilimiting values above which the serviceability of the diode repeated on a maximum junction temperature of 150 degree by limits. The factory should be consulted on applications in	BAV70 BAV74 may be impaired.	70 50 200 1.0 2.0 -55 to +150 150	V V mA A A C

Symbol	Parameter		Test Conditions	Min.	Max.	Units
V _R	Breakdown Voltage	BAV70 BAV74	I _R = 100μA I _R = 5.0μA	75 50		V V
/ _F	Forward Voltage	BAV70 BAV74	$I_{F} = 1.0mA$ $I_{F} = 10mA$ $I_{F} = 50mA$ $I_{F} = 150mA$ $I_{F} = 100mA$		715 855 1.0 1.25 1.0	mV mV V V V
R	Reverse Leakage	BAV70 BAV74	$V_{R} = 25V, T_{A} = 150^{\circ}C$ $V_{R} = 70V$ $V_{R} = 70V, T_{A} = 150^{\circ}C$ $V_{R} = 50V$ $V_{R} = 50V, T_{A} = 150^{\circ}C$		60 5.0 100 100 100	μΑ μΑ μΑ nA μΑ
C _T	Total Capacitance	BAV70 BAV74	$V_R = 0V$, f = 1.0MHz $V_R = 0V$, f = 1.0MHz		1.5 2.0	pF pF
rr	Reverse Recovery Time	BAV70 BAV74			6.0 4.0	ns ns

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BAV70 / 74

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